

LEGM200BH120L2S

IGBT Power Module

Features

- $V_{CE}=1200V$ $I_C=200A$
- Low $V_{CE(sat)}$
- V_{CEsat} with positive temperature coefficient
- Maximum junction temperature $175^{\circ}C$
- Isolation Type Package

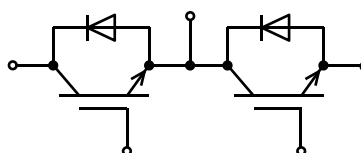
Applications

- The inverter
- Motor control and drives

Package Type & Internal Circuit



L2



Internal Circuit

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CES}	Maximum Power Dissipation	$V_{EC}=0V, I_C=1mA, T_{vj}=25^{\circ}C$	1200	V
I_C	Continuous Collector Current	$T_C=100^{\circ}C$	200	A
I_{CRM}	Peak Collector Current	$I_{CRM}=2I_C$	400	A
V_{GES}	Gate-Emitter Voltage	$T_{vj}=25^{\circ}C$	± 30	V
P_{tot}	Total Power Dissipation	$T_C=25^{\circ}C, T_{vjmax}=175^{\circ}C$	1071	W

Maximum Rated Values (IGBT Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$		1.63		V
		$I_C=200\text{ A}, V_{GE}=15\text{ V}, T_{vj}=150\text{ }^{\circ}\text{C}$		2.03		V
$V_{GE(th)}$	Gate Threshold Voltage	$I_C=3.5\text{ mA}, V_{CE}=V_{GE}, T_{vj}=25\text{ }^{\circ}\text{C}$	5.0	5.9	7.0	V
I_{CES}	Collector-Emitter Cut-off Current	$V_{CE}=1200\text{ V}, V_{GE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{CE}=0\text{ V}, V_{GE}=15\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$			450	nA
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C=200\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=5\text{ }\Omega$ $T_{vj}=25\text{ }^{\circ}\text{C}$		70.8		ns
t_r	Rise Time, Inductive Load			50.4		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			303		ns
t_f	Fall Time, Inductive Load			74		ns
E_{on}	Turn-on Energy Loss per Pulse			10.6		mJ
E_{off}	Energy Loss per Pulse			8.76		mJ
$t_{d(on)}$	Turn-on Delay Time, Inductive Load	$I_C=200\text{ A}, V_{CE}=600\text{ V}$ $V_{GE}=\pm 15\text{ V}$ $R_G=5\text{ }\Omega$ $T_{vj}=150\text{ }^{\circ}\text{C}$		67		ns
t_r	Rise Time, Inductive Load			61		ns
$t_{d(off)}$	Turn-off Delay Time, Inductive Load			336		ns
t_f	Fall Time, Inductive Load			113		ns
E_{on}	Turn-on Energy Loss per Pulse			28.0		mJ
E_{off}	Energy Loss per Pulse			21.6		mJ
R_{thJC}	Thermal resistance, junction to case	per IGBT			0.14	K/W
$T_{vj\text{ op}}$	Temperature under switching conditions		-40		150	$^{\circ}\text{C}$

Maximum Rated Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	$T_{vj}=25\text{ }^{\circ}\text{C}$		1200		V
I_F	Continuous DC Forward Current	$T_C=100\text{ }^{\circ}\text{C}$		100		A
I_{FRM}	Repetitive Peak Forward Current	$t_p=1\text{ ms}$		200		A

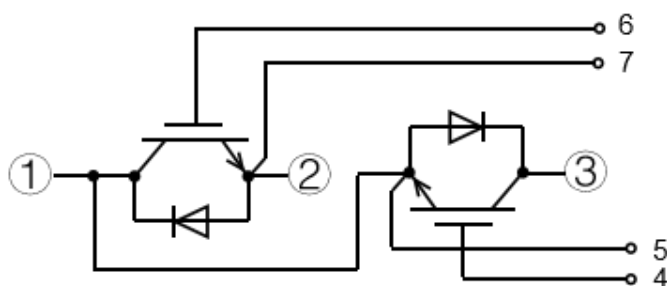
Characteristic Values (Diode Inverter)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Forward Voltage	$I_F=100\text{ A}, V_{CE}=0\text{ V}, T_{vj}=25\text{ }^{\circ}\text{C}$		1.9		V
		$I_F=100\text{ A}, V_{CE}=0\text{ V}, T_{vj}=150\text{ }^{\circ}\text{C}$		1.5		V
I_{rr}	Peak reverse recovery current	$I_F=100\text{ A}, V_R=600\text{ V}$ -di/dt=1270 A/us $T_{vj}=25\text{ }^{\circ}\text{C}$		124		A
Q_r	Recovered Charge			9.82		uC
E_{rec}	Reverse Recovery Energy			3.20		mJ
I_{rr}	Peak reverse recovery current	$I_F=100\text{ A}, V_R=600\text{ V}$ -di/dt=1270 A/us $T_{vj}=150\text{ }^{\circ}\text{C}$		144		A
Q_r	Recovered Charge			17.2		uC
E_{rec}	Reverse Recovery Energy			6.34		mJ
R_{thJC}	Thermal resistance, junction to case	per Diode			0.33	K/W
$T_{vj\text{ op}}$	Operating Junction Temperature		-40		150	$^{\circ}\text{C}$

Module Characteristics

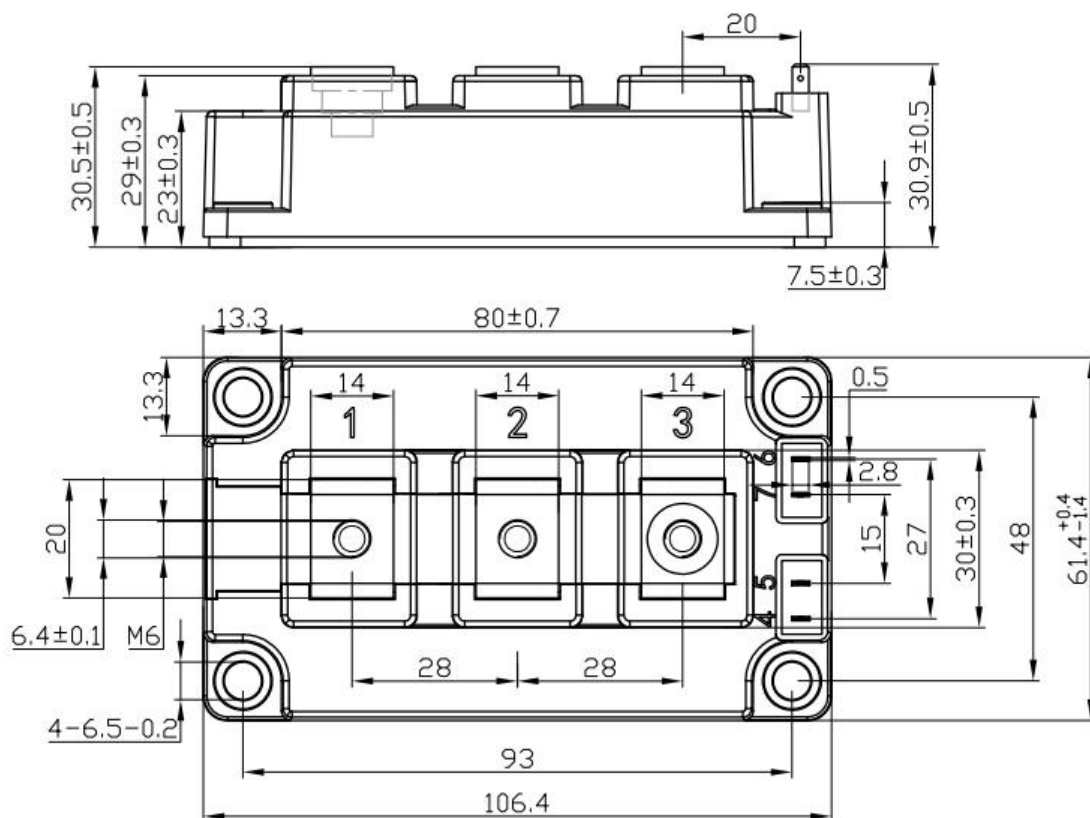
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{isol}	Isolation voltage	$t=1\text{ min}, f=50\text{ Hz}$	2500			V
T_{stg}	Storage Temperature		-40		125	$^{\circ}\text{C}$
M_t	Module Electrodes Torque	Recommended(M5)	2.5		5.0	N·m
M_s	Module-to-Sink Torque	Recommended(M6)	3.0		6.0	N·m
G	Weight of Module			317		g

Circuit Diagram



Package Dimensions

(Dimensions in Millimeters)



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2. Operating conditions may differ from simulation assumptions in several aspects like level of DC-link voltage, applied gate-voltage and gate-resistor, case and junction temperatures as well as the power circuit stray-inductance. Therefore, deviations of parameters and assumptions used for the simulation and the real application may exist.
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